



AOWF4S60 Information



For Reference Only

Part Number AOWF4S60

ManufacturerAlpha & Omega Semiconductor Inc.CategoryDiscrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 600V 4A TO262F

Package TO-262-3 Long Leads, I2Pak, TO-262AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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AOWF4S60 Specifications

Manufacturer Part Number AOWF4S60 Manufacturer Alpha & Omega Semiconductor Inc. Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-262-3 Long Leads, 12Pak, TO-262AA Series aMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 4A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 263pF @ 100V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 25W (Tc) Rds On (Max) @ Id, Vgs 900 mOhm @ 2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package - Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA		
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SeriesaMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.1V @ 250μAGate Charge (Qg) (Max) @ Vgs6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds263pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)25W (Tc)Rds On (Max) @ Id, Vgs900 mOhm @ 2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package-Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.1V @ 250μAGate Charge (Qg) (Max) @ Vgs6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds263pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)25W (Tc)Rds On (Max) @ Id, Vgs900 mOhm @ 2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package-Package / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	Package	TO-262-3 Long Leads, I2Pak, TO-262AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.1V @ 250μAGate Charge (Qg) (Max) @ Vgs6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds263pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)25W (Tc)Rds On (Max) @ Id, Vgs900 mOhm @ 2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package-Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Series	aMOS?
Drain to Source Voltage (Vdss)600 VCurrent - Continuous Drain (Id) @ 25°C4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10 VVgs(th) (Max) @ Id4.1 V @ 250μAGate Charge (Qg) (Max) @ Vgs6n C @ 10 VInput Capacitance (Ciss) (Max) @ Vds263pF @ 100 VVgs (Max)±30 VFET Feature-Power Dissipation (Max)25W (Tc)Rds On (Max) @ Id, Vgs900 mOhm @ 2A, 10 VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package-Package / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 263pF @ 100V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 900 mOhm @ 2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package - Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.1V @ 250μAGate Charge (Qg) (Max) @ Vgs6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds263pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)25W (Tc)Rds On (Max) @ Id, Vgs900 mOhm @ 2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package-Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Drain to Source Voltage (Vdss)	600V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 4.1V @ 250μA 6nC @ 10V 263pF @ 100V 253V 263pF @ 100V 253V 263pF @ 100V 253V 255V To 150°C 150	Current - Continuous Drain (Id) @ 25°C	4A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Power Discover Package To-262-3 Long Leads, I2Pak, TO-262AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA	Vgs(th) (Max) @ Id	4.1V @ 250μA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 25W (Tc) Rds On (Max) @ Id, Vgs 900 mOhm @ 2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package - Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Gate Charge (Qg) (Max) @ Vgs	6nC @ 10V
FET Feature - Cover Dissipation (Max) 25W (Tc) Rds On (Max) @ Id, Vgs 900 mOhm @ 2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package - TO-262-3 Long Leads, I2Pak, TO-262AA	Input Capacitance (Ciss) (Max) @ Vds	263pF @ 100V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 900 mOhm @ 2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package - Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs900 mOhm @ 2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package-Package / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package - Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Power Dissipation (Max)	25W (Tc)
Mounting Type Through Hole Supplier Device Package - Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Rds On (Max) @ Id, Vgs	900 mOhm @ 2A, 10V
Supplier Device Package - Package / Case - TO-262-3 Long Leads, I2Pak, TO-262AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Mounting Type	Through Hole
	Supplier Device Package	-
Report errors?	Package / Case	TO-262-3 Long Leads, I2Pak, TO-262AA
		Report errors?

AOWF4S60 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

AOWF4S60 Payment Methods



















AOWF4S60 Shipping Methods













If you have any question about AOWF4S60, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com